

Title (en)

THIN-LAYERED SEMICONDUCTOR STRUCTURE COMPRISING A HEAT DISTRIBUTION LAYER

Title (de)

HALBLEITER-DÜNNSCHICHTSTRUKTUR MIT EINER SCHICHT ZUR WÄRMEVERTEILUNG

Title (fr)

STRUCTURE SEMICONDUCTRICE EN COUCHE MINCE COMPORANT UNE COUCHE DE REPARTITION DE CHALEUR

Publication

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Application

EP 99929439 A 19990708

Priority

- FR 9901659 W 19990708
- FR 9808919 A 19980710

Abstract (en)

[origin: FR2781082A1] The invention concerns a thin layered semiconductor structure comprising a surface semiconductor layer (2) separated from a support substrate (1) by an intermediate zone (3), said intermediate zone (3) being a multilayer electrically insulating the surface semiconductor layer from the support substrate. The intermediate zone has an interface electrical property considered to be sufficiently good with the surface semiconductor layer and comprises at least a first layer, having suitable thermal conductivity for ensuring the proper functioning of the electronic device(s) which are to be produced from the surface semiconductor layer (2), the intermediate zone further including a second layer, insulating and with low dielectric constant, located between the first layer and the support substrate.

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IPC 8 full level

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